

MAR 16 2005

INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Application No.	10/800,417
		Filing Date	March 11, 2004
		First Named Inventor	Chantal J. Arena
		Art Unit	2812
(Multiple sheets used when necessary)		Examiner	Unknown
SHEET 1 OF 3		Attorney Docket No.	ASMEX.446A

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
S.W.S.	1	6,646,073	04/2003 11/2003	Kendo-Farrer et al.,	
S.W.S.	2	6,709,901	03/2004	Yamazaki, et al.	
S.W.S.	3	2002/0173130 A1	11/2002	Pomerede, et al.	
S.W.S.	4	3,602,778	08/31/71	Ura, et al	
S.W.S.	5	3,720,877	03/13/73	Zarowin	
S.W.S.	6	3,729,645	04/24/73	Redington	
S.W.S.	7	3,737,739	06/05/73	Blakeslee, et al.	
S.W.S.	8	3,984,718	10/05/76	Fein, et al.	
S.W.S.	9	3,984,857	10/05/76	Mason	
S.W.S.	10	3,985,590	10/12/76	Mason	
S.W.S.	11	4,461,820	07/24/84	Shirai, et al.	
S.W.S.	12	4,656,013	04/07/87	Hiai, et al.	
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S.W.S.	15	4,803,186	02/07/89	Chen, et al.	
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S.W.S.	18	4,983,274	01/08/91	Chen, et al.	
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S.W.S.	29	5,667,586	09/16/97	Ek, et al.	

Examiner Signature <i>Stephen W. Smoot</i>	Date Considered October 14, 2005
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*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Multiple sheets used when necessary)

SHEET 2 OF 3

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S.W.J.	30	5,818,100	10/06/98	Grider, et al.	
S.W.J.	31	6,242,080 B1	06/05/01	Kondo	
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S.W.J.	33	6,515,219 B2	02/04/03	Kondo	
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Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T ¹
S.W.J.	40	JP 62017004	01/26/87	Japan		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
S.W.J.	41	TAKAGI ET AL., "Device structure and electrical characteristics of strained-Si-on-insulator (strained-SOI) MOSFETs", Materials Science and Engineering B89 (2002), pp. 426-434	
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Examiner Signature

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O I P E M A R 1 6 2 0 0 5 I N F O R M A T I O N D I S C L O S U R E S T A T E M E N T B Y A P P L I C A N T (Multiple sheets used when necessary)		Application No. 10/800,417
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SHEET 3 OF 3		Examiner Unknown
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
S.W.S.	47	TSUTOMU TEZUKA, "Strained Si- and SiGe-MOSFETs on SiGe-on-insulator (SGOI) substrates", 2002 Japan Epitaxial Technology Symposium, "Advanced Substrate Engineering and Device Technology", February 27, 2002	
S.W.S.	48	TEZUKA ET AL., "Fabrication of strained Si on an ultrathin SiGe-on-insulator virtual substrate with a high-Ge fraction", Applied Physics Letters, Vol 79, No. 12, September 17, 2001, pp. 1798-1800	
S.W.S.	49	TEZUKA ET AL., "Fabrication of a strained Si on sub-10-nm-thick SiGe-on-insulator virtual substrate", Materials Science and Engineering B89 (2002), pp. 360-363	
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S.W.S.	56	ISHIKAWA, Y. ET AL., "Strain-induced band gap shrinkage in Ge grown on Si substrate", Applied Physics Letters, Volume 82, Number 12, March 31, 2003, pp. 2044-2046.	
S.W.S.	57	LEE ET AL., "Growth of strained Si and strained Ge heterostructures on relaxed Si _{1-x} Ge _x by ultrahigh vacuum chemical vapor deposition", J. Vac. Sci. Technol. B 22(1) (Jan/Feb 2004), pp. 158-164.	
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